

REMARKS

Claims 1-3 and 5-11 are pending in this application.

Removal of Issue of 35 U.S.C. § 102(a)

Claims 1-3 and 5-11 have been rejected under 35 U.S.C. § 102(a) as being anticipated Kodama '091 (USP 6,492,091). It is submitted for the reasons stated below that the basis for this rejection has been removed.

Enclosed with this Reply is an English translation of the Priority Document for the present application (Japanese Application No. 2000-352770 filed on November 20, 2000 in Japan). It is submitted that this English translation supports the full scope of the present claims such that applicants have perfected the claim to priority under 35 U.S.C. § 119 so as to establish an effective filing date of November 20, 2000.

Kodama '091 has an effective prior art date of August 6, 2001. In view of the submission of the above-noted English translation of the Priority Document, Kodama '091 has been removed as effective prior art. Consequently, it is requested that this rejection be withdrawn.

It is submitted for the reasons stated above that the outstanding issues in connection with this application have been

resolved so that this application may now be placed into condition for allowance.

Pursuant to 37 C.F.R. §§ 1.17 and 1.136(a), Applicant(s) respectfully petition(s) for a one (1) month extension of time for filing a reply in connection with the present application, and the required fee of \$110.00 is attached hereto.

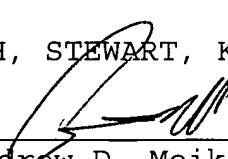
Should there be any outstanding matters that need to be resolved in the present application, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below, to conduct an interview in an effort to expedite prosecution in connection with the present application.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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Attachment: Declaration and verified English translation of Priority Document



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D E C L A R A T I O N

I, Kinshiro TSUKUDA, a national of Japan, c/o Sumitomo Chemical Intellectual Property Service, Limited, 5-33, Kitahama 4-chome, Chuo-ku, Osaka-shi, Osaka 541-8550, Japan, declare that to the best of my knowledge and belief the attached is a full, true and faithful translation into English made by me of the certified copy of Japanese Patent Application No.2000-352700 attached thereto.

Signed this 3rd day of December, 2003

A handwritten signature in black ink, appearing to read "Kinshiro TSUKUDA".

Kinshiro TSUKUDA

PATENT OFFICE
JAPANESE GOVERNMENT

This is to certify that the annexed is a true copy of the following application as filed with this Office.

Date of Application : 20 November, 2000
Application Number : Japanese Patent Application
No. 2000-352700
Applicant(s) : SUMITOMO CHEMICAL COMPANY, LIMITED

26 October, 2001

Commissioner,
Patent Office Kozo, OIKAWA(seal)
(Certificate No.2001-3095040)

Patent Application No.2000-352700

[Name of Document] Patent Application

[Reference Number] P152201

[Date of Submission] 20 November, 2000

[Addressee] Commissioner,
Patent Office

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H01L 21/027

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[List of Articles Filed]

[Name of Article] Specification 1

[Name of Article] Abstract 1

[Number of General Power] 9903380

[Necessity of Proof] Necessary

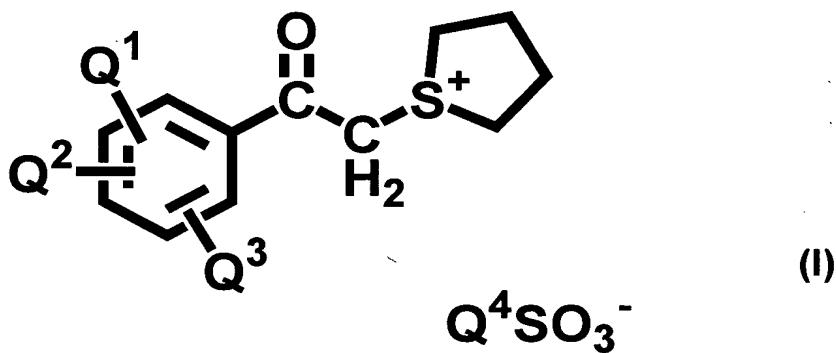
[DOCUMENT NAME] Specification

[TITLE OF THE INVENTION] CHEMICALLY AMPLIFYING TYPE POSITIVE RESIST COMPOSITION

[SCOPE OF CLAIMS]

5 [Claim 1]

A chemically amplifying type positive resist composition comprising a resin which has an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group, and which, *per se*, is insoluble or slightly soluble in alkali 10 but becomes soluble in alkali by the action of an acid; and a sulfonium salt type acid generating agent represented by the following formula (I):

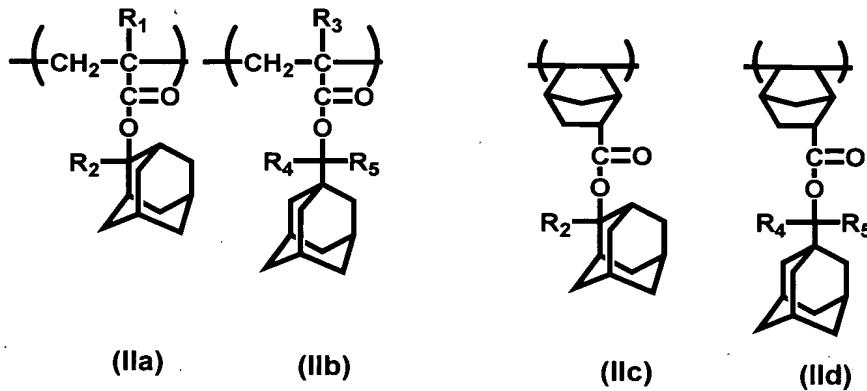


wherein Q¹, Q² and Q³ independently represent hydrogen, hydroxyl, 15 alkyl having 1 to 6 carbon atoms or alkoxy having 1 to 6 carbon atoms; and Q⁴ represents perfluoroalkyl which may have a cyclic structure.

[Claim 2]

The positive resist composition according to claim 1 wherein 20 as the resin, which has an alkali-soluble group protected by

2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group, and which, per se, is insoluble or slightly soluble in alkali but becomes soluble in alkali by the action of an acid, a copolymer comprises any of polymerization unit selected from those 5 represented by the following formula (IIa), (IIb), (IIc) or (IIId):



wherein R₁ and R₃ represent hydrogen or methyl; and R₂ to R₅ represent alkyl.

10 [Claim 3]

The positive resist composition according to claim 1 wherein Q⁴ in the formula (I) is perfluoroalkyl which has 4 or more carbon atoms and which may have a cyclic structure.

[DETAILED DESCRIPTION OF THE INVENTION]

15 [0001]

[TECHNICAL FIELD TO WHICH THE INVENTION PERTAINS]

The present invention relates to a chemical amplifying type positive resist composition used in the minute processing of a semiconductor.

20 [0002]

[PRIOR ART]

A lithography process using a resist composition has usually been adopted in the minute processing of a semiconductor.

In the lithography, the resolution can be improved with a
5 decrease in wavelength of exposure light in principle as
expressed by the equation of Rayleigh's diffraction limit. A
g-line with a wavelength of 436 nm, an i-line with a wavelength
of 365 nm, and a KrF excimer laser with a wavelength of 248
nm have been adopted as exposure light sources for lithography
10 used in the manufacture of a semiconductor. Thus, the
wavelength has become shorter year by year. An ArF excimer
laser having a wavelength of 193 nm is considered to be promising
as a next-generation exposure light source.

[0003]

15 A lens used in an ArF excimer laser exposure machine has
a shorter lifetime as compared with lenses for conventional
exposure light sources. Accordingly, the shorter time required
for exposure to ArF excimer laser light is desirable. For this
reason, it is necessary to enhance the sensitivity of a resist.
20 Consequently, there has been used a so-called chemical
amplifying type resist, which utilizes the catalytic action
of an acid generated by exposure and contains a resin having
a group cleavable by the acid.

[0004]

25 It is known that, desirably, resins used in a resist
for ArF excimer laser exposure have no aromatic ring in order
to ensure the transmittance of the resist, but have an alicyclic

ring in place of an aromatic ring in order to impart a dry etching resistance thereto. Various kinds of resins such as those described in Journal of Photopolymer Science and Technology,

Vol. 9, No. 3, pages 387-398 (1996) by D. C. Hofer, are heretofore

5 known as such resins.

[0005]

Particularly, it has been reported that when a polymer or copolymer having an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group

10 as disclosed in Journal of Photopolymer Science and Technology,

Vol. 9, No. 3, pages 475-487 (1996) by S. Takechi et al., and JP-A-9-73173 is used as a resin of a chemical amplifying type, a high dry etching resistance and a high resolution as well as a good adhesion to a substrate can be attained.

15 [0006]

In fact, a polymer or copolymer having an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group provides a high contrast and a high resolution. However, such a resin has a defect that

20 the top of profile is liable to be broadened in T-top shape.

It is considered that the cause of this defect resides in a bad affinity between a developing solution and a resin due to a strong hydrophobicity of the adamantyl group as well as deactivation of the acid on the resist surface due to basic

25 substances in the surrounding atmosphere. In order to resolve this problem, it is known that a good result may be obtained by adding a much amount of a basic quencher substance. The

addition of a much amount of a quencher substance, however, causes lowering in resolution.

[0007]

[PROBLEMS TO BE SOLVED BY THE INVENTION]

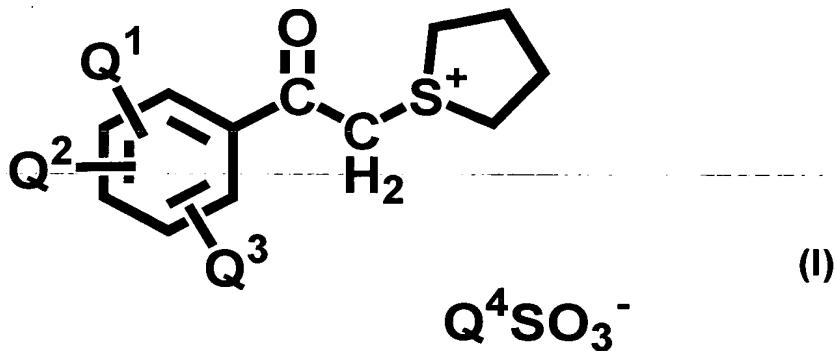
5 An object of the present invention is to provide a chemically amplifying type positive resist composition containing a resin component and an acid generating agent, which is suitable for use in eximer laser lithography such as ArF, KrF or the like, and is satisfactory in various resist 10 performance characteristics such as sensitivity, resolution, and adhesion to a substrate as well as providing an excellent profile shape.

[0008]

[MEANS FOR SOLVING THE PROBLEM]

15 That is to say, the present invention provides a chemically amplifying type positive resist composition comprising a resin which has an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group, and which, per se, is insoluble or slightly soluble in alkali 20 but becomes soluble in alkali by the action of an acid; and a sulfonium salt acid generating agent represented by the following formula (I):

[0009]



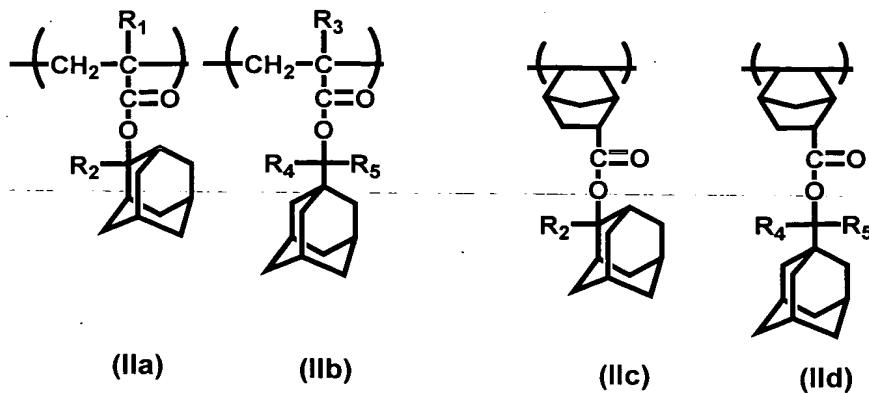
[0010]

wherein Q^1 , Q^2 and Q^3 independently represent hydrogen, hydroxyl, alkyl having 1 to 6 carbon atoms or alkoxy having 1 to 6 carbon atoms; and Q^4 represents perfluoroalkyl which may have a cyclic structure.

[0011]

[EMBODIMENT OF THE INVENTION]

The resin for constituting the resist composition of the present invention is a resin which has an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group, and which, *per se*, is insoluble or slightly soluble in alkali but becomes soluble in alkali due to the action of an acid. The alkali-soluble group includes carboxylic acid group, phenol group, hexafluoroisopropanol group and the like. Usually carboxylic acid group is used for ArF resists. Specific examples include resins having a polymerization unit represented by the following formula (IIa), (IIb), (IIc) and (IId):



wherein R₁ and R₃ represent hydrogen or methyl; and R₂ - R₅ represent alkyl.

[0012]

The polymerization units represented by the formulae
5 (IIa) to (IId) secure transmittance of the resist and contribute
to improvement of dry etching resistance in virtue of the
presence of adamantine ring which is an alicyclic ring. In
addition, 2-alkyl-2-adamantyl group and
1-adamantyl-1-alkylalkyl group in the units are cleaved by the
10 action of an acid to generate a carboxylic acid. Therefore,
the units contribute to enhancement of solubility of a resist
film in alkali after exposure to a light.

R₂ in the formulae (IIa) to (IId) is alkyl. This alkyl can have, for example, about 1 to 8 carbon atoms. Usually, alkyl has advantageously a straight chain but may have a branched chain when it has three or more carbon atoms. Specific examples of R₂ includes methyl, ethyl, propyl, isopropyl, butyl and the like. Amongst them, a resin having methyl or ethyl, inter alia ethyl, as R₂ is preferable for adhesion of resists to a substrate and improvement in resolution.

Specific examples of monomers for leading to the polymerization units represented by the formulae (IIa) to (IId) include 2-methyl-2-adamantyl acrylate, 2-ethyl-2-adamantyl acrylate, 2-methyl-2-adamantyl methacrylate, 5 2-ethyl-2-adamantyl methacrylate, 1-adamantyl-1-methylethyl acrylate, 1-adamantyl-1-methylethyl methacrylate, 2-methyl-2-adamantyl 5-norbornene-2-carboxylate, 2-ethyl-2-adamantyl 5-norbornene-2-carboxylate, 1-(1-adamantyl)-1-methylethyl 5-norbornene-2-carboxylate 10 and the like. Use of 2-adamantyl-2-alkyl (meth)acrylate as a monomer is particularly preferred because it provides an excellent resolution.

[0013]

The resin may have a polymerization unit of monomers, 15 such as those listed below, in addition to the above described polymerization units.

[0014]

3-hydroxy-1-adamantyl (meth)acrylate, 3,5-dihydroxy-1-adamantyl (meth)acrylate, 20 α -(meth)acryloyloxy- γ -butyrolactone, β -(meth)acryloyloxy- γ -butyrolactone, maleic anhydride, itaconic anhydride, 5-(meth)acryloyloxy-2,6-norbornanecarbolactone, 25 2-norbornene, 2-hydroxy-5-norbornene, 5-norbornene-2-carboxylic acid,

methy1 5-norbornene-2-carboxylate,
t-butyl 5-norbornene-2-carboxylate,
1-cyclohexyl-1-methylethyl
5-norbornene-2-carboxylate,
5 1-(4-methylcyclohexyl)-1-methylethyl
5-norbornene-2-carboxylate,
1-(4-hydroxycyclohexyl)-1-methylethyl
5-norbornene-2-carboxylate,
10 1-methyl-1-(4-oxocyclohexyl)ethyl
5-norbornene-2-carboxylate,
1-(1-adamantyl)-1-methylethyl
5-norbornene-2-carboxylate,
1-methylcyclohexyl 5-norbornene-2-carboxylate,
2-methyl-2-adamantyl 5-norbornene-2-carboxylate,
15 2-ethyl-2-adamantyl 5-norbornene-2-carboxylate,
2-hydroxy-1-ethyl 5-norbornene-2-carboxylate,
5-norbornene-2-methanol,
5-norbornene-2,3-dicarboxylic acid anhydride,
(meth)acrylonitrile and the like.
20 [0015]
Generally, the resin for the chemically amplifying type positive resist composition per se, is insoluble or slightly soluble in alkali. However, a part of groups is cleaved by the action of an acid and after then becomes soluble in alkali.
25 In the resin specified in the present invention, 2-alkyl-2-adamantyl group and 1-adamantyl-1-alkylalkyl group are cleaved by the action of an acid. Therefore, resist

compositions containing such a resin work positively. If necessary, the resin may contain another polymerization unit which is cleaved by the action of an acid.

Examples of another unit which is cleaved by the action

5 of an acid include various esters of carboxylic acid, such as, alkyl esters exemplified by methyl ester and tert-butyl ester; acetal type esters such as methoxymethyl ester, ethoxymethyl ester, 1-ethoxyethyl ester, 1-isobutoxyethyl ester, 1-isopropoxyethyl ester, 1-ethoxypropyl ester,
10 1-(2-methoxy)ethoxyethyl ester, 1-(2-acetoxyethoxy)ethyl ester, 1-[2-(1-adamantyloxy)ethoxy]ethyl ester, 1-[2-(1-adamantanecarbonyloxy)ethoxy]ethyl ester, tetrahydro-2-furyl ester and tetrahydro-2-pyranyl ester; alicyclic esters such as isobornyl ester; and the like.

15 Monomers for leading to polymerization units having these carboxylic acid esters may either be acrylic derivatives such as methacrylic acid esters and acrylic acid esters or compounds in which a carboxylic acid ester group is bound to an alicyclic monomer such as norbornenecarboxylic acid ester,
20 tricyclodecenecarboxylic acid ester and tetracyclodecenecarboxylic acid ester.

[0016]

While the resin used in the invention varies depending on the kind of radiation for patterning exposure or group
25 cleavable by the action of acid, it is generally preferred that the resin contains a polymerization unit having a group cleavable by the action of an acid within a range of 30 to 80% by mole.

In addition, it is particularly advantageous that 20% by mole or more of the polymerization unit represented by the formulae (IIa), (IIb), (IIc) or (IId) based on the total resin is contained as a group cleavable by the action of an acid.

5 [0017]

The acid generating agent, which is the other component of the resist composition, is a substance which is decomposed to generate an acid by applying a radiation such as a light, an electron beam or the like on the substance itself or on a 10 resist composition containing the substance. The acid generated from the acid generating agent acts on said resin resulting in cleavage of the group cleavable by the action of an acid existing in the resin. In the present invention, a sulfonium salt compound represented by the formula (I) shown 15 before is used as the acid generating agent.

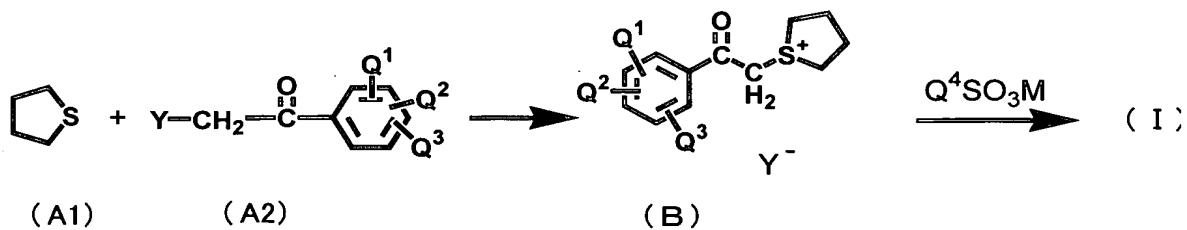
[0018]

In the formula (I), Q^1 , Q^2 and Q^3 independently represent hydrogen, hydroxyl, alkyl having 1 to 6 carbon atoms or alkoxy having 1 to 6 carbon atoms. When alkyl or alkoxy has three 20 or more carbon atoms, they may either be straight chain or branched chain. Specific examples of alkyl include methyl, ethyl, propyl, isopropyl, butyl, tert-butyl, pentyl, hexyl and the like; and examples of alkoxy include methoxy, ethoxy, propoxy, butoxy and the like. By using these compounds as the acid 25 generating agent, T-top shape in the profile of resist becomes indistinct.

[0019]

The sulfonium salt represented by the formula (I) can be produced according to a known process. For example, the salt can be produced according to the following reaction scheme applying a method described in *J. Polymer Science, Polymer Chemistry Edition*, Vol. 17, 2877 - 2892 (1979) by J. V. Crivello, et al.

[0020]



[0021]

wherein Q^1 , Q^2 , Q^3 and Q^4 are as defined above, Y represents halogen such as bromine or iodine, and M represents alkali metal such as sodium and potassium or silver.

[0022]

Briefly, the sulfonium salt represented by the formula
(I) can be obtained by reacting a β -halogenoketone corresponding
15 to the above formula (A2) on a sulfide compound corresponding
to the above formula (A1) to give a sulfonium halide
corresponding to the above formula (B), followed by the action
of sulfonic acid metal salt corresponding to the formula Q^4SO_3M .
These reactions are carried out in an appropriate solvent such
20 as acetone, acetonitrile, nitromethane or the like. The
sulfide compound of the formula (A1) is used preferably in 0.7
to 1.5 molar ratio, more preferably in 0.8 to 1.1 molar ratio,
based on the β -halogenoketone of the formula (A2). The sulfonic

acid metal salt of the formula Q^4SO_3M may be used preferably in 0.7 to 1.2 molar ratio, more preferably in 0.8 to 1.0 molar ratio, based on the sulfide compound used for formation of the sulfonylum halide of the formula (B). After the reaction is 5 completed, the sulfonylum salt of the formula (I) can be obtained by removing the produced metal halide by filtration or others, and then applying post-treatment such as concentration, recrystallization or the like.

[0023]

10 In the formula (I), examples of perfluoroalkylsulfonate anion optionally having cyclic structure in the formula (I) include trifluoromethanesulfonate ion, perfluorobutanesulfonate ion, perfluoroctanesulfonate ion, perfluorocyclohexanesulfonate ion, 15 perfluoro-4-ethylcyclohexanesulfonate ion and the like. Preferably, the perfluoroalkylsulfonate anion has 4 or more carbon atoms, because a distance of diffusion of the acid is shorter and the resolution is better.

[0024]

20 The resist composition of the invention is a combination of a resin which has an alkali-soluble group protected by 2-alkyl-2-adamantyl group or 1-adamantyl-1-alkylalkyl group, and which, per se, is insoluble or slightly soluble in alkali but becomes soluble in alkali due to the action of an acid, 25 and a sulfonylum salt represented by the above described formula (I) as an acid generating agent. If desired, another acid generating agent can be co-used together with the sulfonylum

salt.

Another acid generating agent which can be co-used, for example, includes other onium salt compounds such as sulfonium salts other than the sulfonium salt of the formula (I) and 5 iodonium salts. Examples thereof include diphenyliodonium salts, triphenylsulfonium salts, alkylsulfonium salts such as cyclohexylmethyl(2-oxocyclohexyl)sulfonium salts described in JP-A-7-28237, 2-oxobutylthiacyclopentanium salts described in J. Photopolym. Sci. Technol., Vol. 13, No. 2, 235 - 236 (2000) 10 by S. Iwasa, et al; organic halogen compound such as haloalkyltriazine compounds; sulfone compounds such as disulfones and diazomethanedisulfones; various sulfonic acid esters and the like.

[0025]

15 Following compounds can be exemplified as acid generating agents which can be co-used with the sulfonium salt of the formula (I):

diphenyliodonium trifluoromethanesulfonate,
4-methoxyphenylphenyliodonium hexafluoroantimonate,
20 4-methoxyphenylphenyliodonium trifluoromethanesulfonate,
bis(4-tert-butyphenyl)iodonium tetrafluoroborate,
bis(4-tert-butyphenyl)iodonium hexafluorophosphate,
bis(4-tert-butyphenyl)iodonium hexafluoroantimonate,
bis(4-tert-butyphenyl)iodonium trifluoromethanesulfonate,
25 [0026]

triphenylsulfonium hexafluorophosphate,
triphenylsulfonium hexafluoroantimonate,

triphenylsulfonium trifluoromethanesulfonate,
4-methoxyphenyldiphenylsulfonium hexafluoroantimonate,
4-methoxyphenyldiphenylsulfonium trifluoromethanesulfonate,
p-tolyldiphenylsulfonium trifluoromethanesulfonate,
5 p-tolyldiphenylsulfonium perfluorobutanesulfonate,
p-tolyldiphenylsulfonium perfluorooctanesulfonate,
2,4,6-trimethylphenyldiphenylsulfonium
trifluoromethanesulfonate,
4-tert-butylphenyldiphenylsulfonium
10 trifluoromethanesulfonate,
4-phenylthiophenyldiphenylsulfonium hexafluorophosphate,
4-phenylthiophenyldiphenylsulfonium hexafluoroantimonate,
1-(2-naphthoylmethyl)thiolanium hexafluoroantimonate,
1-(2-naphthoylmethyl)thiolanium trifluoromethanesulfonate,
15 4-hydroxy-1-naphthyldimethylsulfonium hexafluoroantimonate,
4-hydroxy-1-naphthyldimethylsulfonium
trifluoromethanesulfonate,
cyclohexylmethyl(2-oxocyclohexyl)sulfonium
trifluoromethanesulfonate,
20 cyclohexylmethyl(2-oxocyclohexyl)sulfonium
perfluorobutanesulfonate,
cyclohexylmethyl(2-oxocyclohexyl)sulfonium
perfluorooctanesulfonate,
[0027]
25 3,3-dimethyl-2-oxobutyl thiacyclopentanium
trifluoromethanesulfonate,
3,3-dimethyl-2-oxobutyl thiacyclopentanium

perfluorobutanesulfonate,

3,3-dimethyl-2-oxobutyl thiacyclopentanium

perfluorooctanesulfonate,

3,3-dimethyl-2-oxobutyl thiacyclopentanium butanesulfonate,

5 3,3-dimethyl-2-oxobutyl thiacyclopentanium

p-toluenesulfonate,

3,3-dimethyl-2-oxobutyl thiacyclopentanium

camphorsulfonate,

3,3-dimethyl-2-oxobutyl dimethylsulfonium

10 perfluorobutanesulfonate,

2-oxobutyl thiacyclopentanium perfluorobutanesulfonate,

dibutyl (3,3-dimethyl-2-oxobutyl) sulfonium

perfluorobutanesulfonate,

3,3-dimethyl-2-oxobutyl thiacyclohexanium

15 perfluorobutanesulfonate,

3,3-dimethyl-2-oxobutyl (1,4-thioxanium)

perfluorobutanesulfonate,

[0028]

2-methyl-4,6-bis(trichloromethyl)-1,3,5-triazine,

20 2,4,6-tris(trichloromethyl)-1,3,5-triazine,

2-phenyl-4,6-bis(trichloromethyl)-1,3,5-triazine,

2-(4-chlorophenyl)-4,6-bis(trichloromethyl)-1,3,5-triazine,

2-(4-methoxyphenyl)-4,6-bis(trichloromethyl)-1,3,5-

triazine,

25 2-(4-methoxy-1-naphthyl)-4,6-bis(trichloromethyl)-1,3,5-

triazine,

2-(benzo[d][1,3]dioxolane-5-yl)-4,6-bis(trichloromethyl)-

1,3,5-triazine,
2-(4-methoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-triazine,
2-(3,4,5-trimethoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-
5 triazine,
2-(3,4-dimethoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-triazine,
2-(2,4-dimethoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-
10 triazine,
2-(2-methoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-triazine,
2-(4-butoxystyryl)-4,6-bis(trichloromethyl)-1,3,5-triazine,
2-(4-pentyloxystyryl)-4,6-bis(trichloromethyl)-1,3,5-
15 triazine,
[0029]
diphenyl disulfone,
di-p-tolyl disulfone,
bis(phenylsulfonyl)diazomethane,
20 bis(4-chlorophenylsulfonyl)diazomethane,
bis(p-tolylsulfonyl)diazomethane,
bis(4-tert-butylphenylsulfonyl)diazomethane,
bis(2,4-xylylsulfonyl)diazomethane,
bis(cyclohexylsulfonyl)diazomethane,
25 (benzoyl)(phenylsulfonyl)diazomethane,
[0030]
1-benzoyl-1-phenylmethyl p-toluenesulfonate (so-called

benzointosylate),

2-benzoyl-2-hydroxy-2-phenylethyl p-toluenesulfonate

(so-called α -methylolbenzointosylate),

1,2,3-benzenetriyl trimethanesulfonate,

5 2,6-dinitrobenzyl p-toluenesulfonate,

2-nitrobenzyl p-toluenesulfonate,

4-nitrobenzyl p-toluenesulfonate,

[0031]

N-(phenylsulfonyloxy)succinimide,

10 N-(trifluoromethylsulfonyloxy)succinimide,

N-(trifluoromethylsulfonyloxy)phthalimide,

N-(trifluoromethylsulfonyloxy)-5-norbornene-2,3-dicarboxyimide,

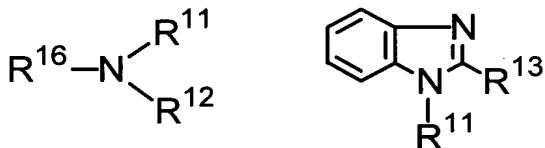
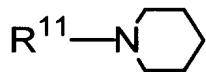
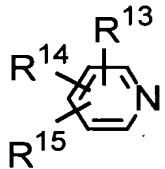
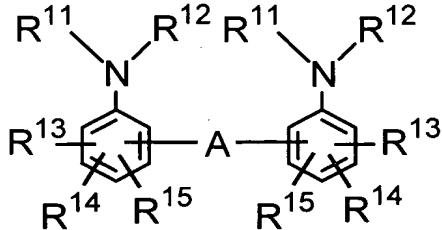
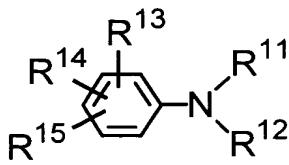
N-(trifluoromethylsulfonyloxy)naphthalimide,

15 N-(10-camphorsulfonyloxy)naphthalimide, and the like.

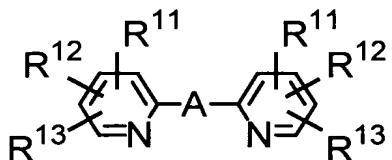
[0032]

It is also known that, generally in a chemical amplifying type positive resist composition, performance deterioration due to the deactivation of an acid associated with leaving after 20 exposure can be reduced by adding basic compounds, especially basic nitrogen-containing organic compounds such as amines as quenchers. It is also preferable in the present invention that such basic compounds are added. Concrete examples of the basic compounds to be used as quenchers include the ones represented 25 by the following formulae:

[0033]



5



[0034]

Wherein R¹¹, R¹², R¹³, R¹⁴ and R¹⁵ represent, independently each other, hydrogen, alkyl optionally substituted with hydroxyl,

10 cycloalkyl optionally substituted with hydroxyl, aryl optionally substituted with hydroxyl or alkoxy optionally substituted with hydroxyl. A represents alkylene, carbonyl or imino. The alkyl and alkoxy in R¹¹ to R¹⁵ may have 1 to 6 carbon atoms, the cycloalkyl thereof may have 5 to 10 carbon atoms, the aryl thereof may have 6 to 10 carbon atoms. The

15

alkylene in A may have 1 to 6 carbon atoms and may be strait chained or branched.

[0035]

The resist composition of the present invention 5 preferably contains the resin in an amount of 80 to 99.9 % by weight, and the acid generating agent in an amount of 0.1 to 20 % by weight based on the total solid component weight of the resist composition. When a basic compound is used as a quencher, it is preferably contained in an amount in the range 10 of 0.01 to 0.1 % by weight based on the total solid component weight of the resist composition. The composition may also contain, if required, a small amount of various additives such as sensitizers, acid amplifiers, dissolution inhibitors, resins other than the above resin, surfactants, stabilizers, dyes, 15 and the like.

[0036]

The resist composition of the present invention generally becomes a resist solution in the state in which the above-described components are dissolved in a solvent to be 20 applied on a substrate such as a silicon wafer. The solvent herein used may be one which dissolves each component, has an appropriate drying rate, and provides a uniform and smooth coating after evaporation of the solvent, and can be one which is generally used in this field. Examples thereof include 25 glycol ether esters such as ethylcellosolve acetate, methylcellosolve acetate, and propylene glycol monomethyl ether acetate; esters such as ethyl lactate, butyl acetate,

amyl acetate, and ethyl pyruvate; ketones such as acetone, methyl isobutyl ketone, 2-heptanone, and cyclohexanone; and cyclic esters such as γ -butyrolactone. These solvents can be used alone or in combination of two or more thereof.

5 [0037]

The resist film applied on a substrate, and dried is subjected to an exposure treatment for patterning. Then, after a heat-treatment for promoting a protecting deblocking reaction, development by an alkali developer is conducted. The alkali developer herein used can be various kinds of alkaline aqueous solutions used in this field. In general, an aqueous solution of tetramethylammoniumhydroxide or (2-hydroxyethyl)trimethylammoniumhydroxide (so-called colline) is often used.

15 [0038]

[Examples]

The present invention will be described in more detail by way of examples, which should not be construed as limiting the scope of the present invention. All % and parts in examples 20 are by weight unless otherwise stated. The weight-average molecular weight is a value determined from gel permeation chromatography using polystyrene as a reference standard.

[0039]

Resin Synthesis Example:

25 A solution was prepared by charging 2-methyl-2-adamantyl methacrylate, 3-hydroxy-1-adamantyl acrylate and hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl

methacrylate in a molar ratio of 5:2.5:2.5 (20.0 parts/9.5 parts/9.5 parts) and adding methyl isobutyl ketone in two times the weight of total monomer. As an initiator, azobisisobutyronitrile was added thereto in an amount of 2%
5 by mole based on the total monomer and the mixture was heated to 85°C for about 6 hours. Then, a treatment in which the reaction solution was poured into a large amount of methanol to cause precipitation was applied and the obtained resin was purified by washing three times the wet cake of resin with methanol.
10 As the result, a copolymer having a weight average molecular weight of about 12,200 was obtained. This resin is referred to as Resin A1.

[0040]

15 Acid generating agent Synthesis Example 1: Synthesis of Acid generating agent B1

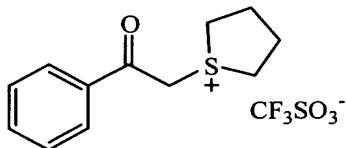
(1) Into a four-necked flask were charged 14.9 parts of phenacyl bromide and 75 parts of acetone, and 6.6 parts of tetrahydrothiophene was added dropwise thereto. The mixture was stirred at room temperature for 18 hours. The obtained 20 crystals were filtered, washed with 80 parts of a mixed solvent consisting of tert-butyl methyl ether and acetone in a ratio 1:1 (weight base), 50 parts of tert-butyl methyl ether and dried to give 16.9 parts of

tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium bromide.

25 (2) Into a four-necked flask were charged 4.00 parts of tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium bromide obtained in (1) and 160 parts of acetonitrile, and 2.62 parts

of potassium trifluoromethanesulfonate was added thereto. The mixture was stirred at room temperature for 18 hours. Precipitated potassium bromide was removed by filtration and the filtrate was concentrated. To this was added 150 parts 5 of chloroform and the mixture was stirred at room temperature for 16 hours. Insoluble matters were removed by filtration. The filtrate was concentrated and 22 parts of acetone was added. Insoluble matters were removed by filtration and the filtrate was concentrated further. The obtained residue from 10 concentration was recrystallized from a mixed solvent of acetone and ethyl acetate to give 3.41 parts of the desired compound. The compound was identified to be tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium trifluoromethanesulfonate represented by the formula shown 15 below by $^1\text{H-NMR}$ ("GX-270", manufactured by JEOL). This is referred to as PAG 1.

[0041]



[0042]

$^1\text{H-NMR}$ (dimethylsulfoxide-d6, internal standard:
20 tetramethylsilane), δ (ppm):
2.16 - 2.32 (m, 4H); 3.46 - 3.64 (m, 4H); 5.31 (s, 2H);
7.63 (m, 2H); 7.77 (m, 1H); 8.00 (m, 2H).

[0043]

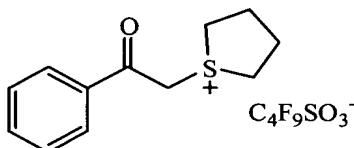
Acid generating agent Synthesis Example 2: Synthesis of Acid

generating agent B2

Into a four-necked flask were charged 5.00 parts of tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium bromide, 50 parts of acetonitrile and 2.5 parts of water, and a solution 5 of 7.08 parts of silver perfluorobutanesulfonate in 21.3 parts of acetonitrile was added thereto. The mixture was stirred at room temperature for 4 hours. Precipitated silver bromide was removed by filtration and the filtrate was concentrated. The obtained residue from concentration was recrystallized from 10 a mixed solvent of ethyl acetate and tert-butyl methyl ether to give 6.77 parts of the desired compound. The compound was identified to be

tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium perfluorobutanesulfonate represented by the formula shown 15 below by $^1\text{H-NMR}$ ("GX-270", manufactured by JEOL). This is referred to as PAG 2.

[0044]



[0045]

$^1\text{H-NMR}$ (chloroform-d1, internal standard: tetramethylsilane), 20 δ (ppm) :

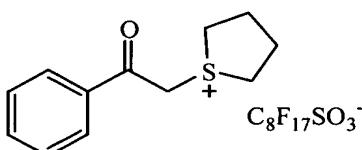
2.23 - 2.36 (m, 2H); 2.42 - 2.53 (m, 2H); 3.59 - 3.77 (m, 4H); 5.35 (s, 2H); 7.45 (m, 2H); 7.63 (m, 1H); 7.99 (m, 2H).

[0046]

Acid generating agent Synthesis Example 3: Synthesis of Acid generating agent B3

Into a four-necked flask were charged 3.00 parts of tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium bromide and 5 120 parts of acetonitrile, and 5.62 parts of potassium perfluorooctanesulfonate was added thereto. The mixture was stirred at room temperature for 24 hours. Precipitated potassium bromide was removed by filtration and the filtrate was concentrated. To this was added 50 parts of chloroform 10 and the mixture was stirred at room temperature for 16 hours. Insoluble matters were removed by filtration. The filtrate was dissolved in 200 parts of chloroform and the obtained chloroform solution was washed with water. After washing, the chloroform layer was concentrated and added dropwise to 15 tert-butyl methyl ether. The obtained crystals were filtered and dried to give 4.66 parts of the desired compound. The compound was identified to be tetrahydro-1-(2-oxo-2-phenylethyl)thiophenium perfluorooctanesulfonate represented by the formula shown 20 below by $^1\text{H-NMR}$ ("GX-270", manufactured by JEOL). This is referred to as PAG 3.

[0047]



[0048]

$^1\text{H-NMR}$ (chloroform-d1, internal standard: tetramethylsilane),

δ (ppm):

2.21 - 2.52 (m, 4H); 3.58 - 3.77 (m, 4H); 5.35 (s, 2H);
7.44 (m, 2H); 7.61 (m, 1H); 7.99 (m, 2H).

[0049]

5 Examples 1 - 4 and Comparative Examples 1 - 3

A resist solution was prepared by mixing an acid generating agent and a resin in a composition and amount shown in Table 1, 2,6-diisopropylaniline as a quencher in an amount shown in Table 1, together with 57 parts of PGMEA (propylene glycol monomethyl ether acetate) and 3 parts of GBL (γ -butyrolactone), and filtering through a filter made of a fluorine resin having a pore diameter of 0.2 μ m.

[0050]

PAG 4: 4-methylphenyldiphenylsulfonium
15 perfluoromethanesulfonate,
PAG 5: 4-methylphenyldiphenylsulfonium
perfluorobutanesulfonate,
PAG 6: 4-methylphenyldiphenylsulfonium
perfluorooctanesulfonate.

20 [0051]

[Table 1]

Example No.	Resin	Acid generating agent	Quencher
Example 1	A1(10 parts)	PAG1(0.3 part)	0.0075 part
Example 2	A1(10 parts)	PAG2(0.43 part)	0.0075 part
Example 3	A1(10 parts)	PAG3(0.6 part)	0.0075 part
Example 4	A1(10 parts)	PAG3(0.6 part)/ PAG6(0.2 part)	0.015 part
Comparative example 1	A1(10 parts)	PAG4(0.11 part)	0.0075 part

Comparative example 2	A1(10 parts)	PAG5(0.135 part)	0.0075 part
Comparative example 3	A1(10 parts)	PAG6(0.2 part)	0.0075 part

* The amounts of the acid generating agent in Examples 1 to 3 and Comparative Examples 1 to 3 were adjusted so that respective amounts were equimolar.

[0052]

5 The above resist solution was spin-coated to a film thickness after drying of 0.39 μm on a silicon wafer on which an organic anti-reflection-layer having a thickness of 1,600 Angstrom was formed by applying "DUV-30J-14" manufactured by Brewer Co. Ltd. and baking under conditions of 215°C and 60
10 seconds. After applying the resist solution, prebaking was carried out on a direct hot plate at 100°C for 60 seconds. The wafer having a resist film formed in this manner was exposed to a line-and-space pattern changing stepwise the irradiation amount. After exposure, post exposure bake was conducted on
15 a hot plate at 130°C for 60 seconds. Further, paddle development was conducted with a 2.38% aqueous solution of tetramethylammonium hydroxide for 60 seconds. The pattern obtained after the development was observed by a scanning electron microscope and its effective sensitivity, profile and
20 resolution were measured according to the following methods.

[0053]

Effective sensitivity: This was shown by the minimum irradiation amount at which a 0.18 μm line-and-space pattern was formed at 1:1.

[0054]

Profile: This was the shape in cross section of 0.18 μm line-and-space pattern at the irradiation amount providing the effective sensitivity.

5 [0055]

Resolution: This was shown by the minimum dimension of a line-and-space pattern separated at the irradiation amount providing the effective sensitivity.

[0056]

10 Separately, the above resist solution was applied on a silicon glass wafer so that a film thickness of 0.39 μm after prebaking under the same conditions as above was formed, and the transmittance of the resist film at 193 nm was measured. The results are shown in Table 2.

15 [0057]

[Table 2]

Example No.	Effective sensitivity	Profile	Resolution	Transmittance
Example 1	50 mJ/cm^2	Rectangular	0.17 μm	70%
Example 2	50 mJ/cm^2	Rectangular	0.15 μm	70%
Example 3	53 mJ/cm^2	Rectangular	0.15 μm	70%
Example 4	39 mJ/cm^2	Rectangular	0.15 μm	59%
Comparative example 1	41 mJ/cm^2	T-top	0.17 μm	68%
Comparative example 2	47 mJ/cm^2	T-top	0.15 μm	68%
Comparative example 3	47 mJ/cm^2	T-top	0.15 μm	67%

[0058]

As shown above, the resists of Examples provided a profile of less T-top and more correct rectangular than the resist of 20 Comparative Examples. In addition, the resists of Examples

resulted less decrease in sensitivity and similar resolution.

[0059]

[Effects of the Invention]

The chemically amplifying type positive resist

5 composition according to the present invention comprises resin component and an acid generating agent, and is suitable for use in the lithography utilizing an ArF or KrF excimer laser. In addition, it is a resist composition having good resist performances such as sensitivity, resolution and adhesion to
10 a substrate and excellent in the shape of profile.

[DOCUMENT NAME] Abstract

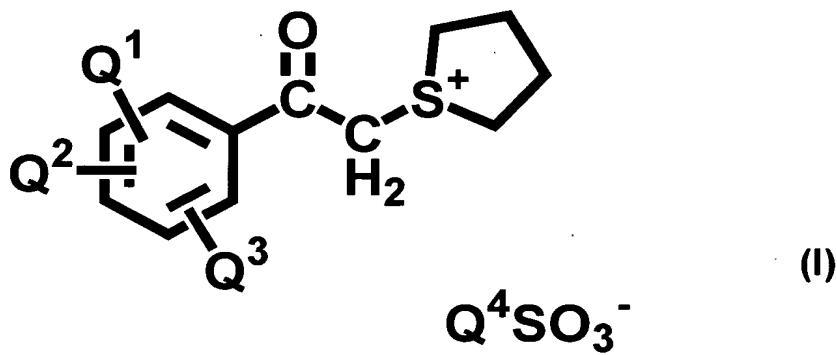
[ABSTRACT]

[PROBLEMS TO BE SOLVED] The chemically amplifying type positive resist composition comprising resin component and an

5 acid generating agent, suitable for use in the lithography utilizing an ArF or KrF excimer laser, having good resist performances such as sensitivity, resolution and adhesion to a substrate, and excellent in the shape of profile is to be provided.

10 [SOLVING MEANS] A chemically amplifying type positive resist composition suitable for use in the lithography utilizing an ArF or KrF excimer laser and excellent in the shape of profile is provided, which comprises a resin which has an alkali-soluble group protected by 2-alkyl-2-adamantyl group or

15 1-adamantyl-1-alkylalkyl group, and which, *per se*, is insoluble or slightly soluble in alkali but becomes soluble in alkali by the action of an acid; and a sulfonium salt acid generating agent represented by the following formula (I):



20 wherein Q^1 , Q^2 and Q^3 independently represent hydrogen, hydroxyl,

alkyl having 1 to 6 carbon atoms or alkoxy having 1 to 6 carbon atoms; and Q⁴ represents perfluoroalkyl which may have a cyclic structure.

[SELECTED DRAWING] None

Patent Application No.2000-352700

[Name of Document] Correction Data

[Document Corrected] Patent Application

[Acknowledged Data • Additional Data]

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